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Correction: Plasma enhanced atomic layer deposition of Ga₂O₃ thin films

Ranjith K. Ramachandran,^a Jolien Dendooven,^a Jonas Botterman,^b Sreeprasanth Pulinthanathu Sree,^c Dirk Poelman,^b Johan A. Martens,^c Hilde Poelman^d and Christophe Detavernier^{*a}

Correction for 'Plasma enhanced atomic layer deposition of Ga₂O₃ thin films' by Ranjith K. Ramachandran *et al.*, *J. Mater. Chem. A*, 2014, 2, 19232–19238.

On the y-axis of Fig. 4, the authors mistyped the unit of thickness as "Å" instead of "nm". This has now been corrected in the new Fig. 4 provided, as shown.

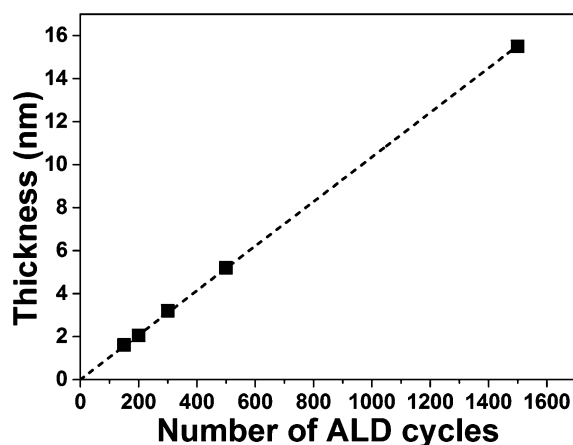


Fig. 4 Thickness of the Ga₂O₃ films deposited at 200 °C on SiO₂/Si substrates against the number of ALD cycles.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

^aDepartment of Solid State Sciences, CoCooN, Ghent University, Krijgslaan 281/S1, 9000 Ghent, Belgium. E-mail: Christophe.detavernier@ugent.be; Fax: +32-9-264-4996; Tel: +32-9-264-4354

^bDepartment of Solid State Sciences, LumiLab, Ghent University, Krijgslaan 281/S1, 9000 Ghent, Belgium

^cCentre for Surface Chemistry and Catalysis, Catholic University of Leuven, Kasteelpark Arenberg 23, B-3001 Leuven, Belgium

^dLaboratory for Chemical Technology, Ghent University, Technologiepark 914, B-9052 Zwijnaarde, Belgium